

SANYO Semiconductors DATA SHEET

STK433-730-E - 2-channel class AB audio power IC, 30W+30W

Overview

The STK433-730-E is a hybrid IC designed to be used in $30W \times 30W$ (2-channel) class AB audio power amplifiers.

Applications

• Audio power amplifiers.

Features

- Miniature package (47.0mm × 25.6mm × 9.0mm)
- Output load impedance: $R_L = 6\Omega$ to 4Ω supported
- Built-in stand-by circuit, output limiting circuit for substrate overheating, and load short-circuit protection circuit constituted by monolithic ICs

Series Models

	STK433-730-E	STK433-760-E			
Output 1 (10%/1kHz)	30W×2 channels	50W×2 channels			
Output 2 (0.4%/20Hz to 20kHz)	15W×2 channels	35W×2 channels			
Max. rated V _{CC} (quiescent)	±30V	±50V			
Max. rated V _{CC} (6 Ω)	±28V	±40V			
Max. rated V _{CC} (4 Ω)	±25V	±33V			
Recommended operating V_{CC} (4 Ω)	±18V	±23V			
Dimensions (excluding pin height)	47.0mm×25.6mm×9.0mm				

- Any and all SANYO Semiconductor Co.,Ltd. products described or contained herein are, with regard to "standard application", intended for the use as general electronics equipment (home appliances, AV equipment, communication device, office equipment, industrial equipment etc.). The products mentioned herein shall not be intended for use for any "special application" (medical equipment whose purpose is to sustain life, aerospace instrument, nuclear control device, burning appliances, transportation machine, traffic signal system, safety equipment etc.) that shall require extremely high level of reliability and can directly threaten human lives in case of failure or malfunction of the product or may cause harm to human bodies, nor shall they grant any guarantee thereof. If you should intend to use our products for applications outside the standard applications, please consult with us prior to the intended use. If there is no consultation or inquiry before the intended use, our customer shall be solely responsible for the use.
- Specifications of any and all SANYO Semiconductor Co.,Ltd. products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.

Specifications

Absolute Maximum Ratings at $Ta = 25^{\circ}C$, $Tc=25^{\circ}C$ unless otherwise specified

Parameter	Symbol	Conditions	Ratings	Unit
Maximum supply voltage V _{CC} max (0)		Stand-by ON or When no signal (Stand-by OFF)	±30	V
	V _{CC} max (1)	When signals are present, $R_L \ge 6\Omega$ (*1)	±28	V
	V _{CC} max (2)	When signals are present, $R_L \ge 4\Omega$ (*1)	±25	V
Minimum operating supply voltage	V _{CC} min		±10	V
Stand-by pin maximum voltage	VST max		-0.3 to +5.5	V
Output current	I _O (peak)	1ch, ton=25ms	4.0	А
Thermal resistance	өј-с	Per power transistor	4.2	0.000
		Per package	1.1	°C/W
Junction temperature	Tj max	Both the Tj max and Tc max conditions must be met.	150	°C
IC substrate operating temperature	Tc max		125	°C
Storage temperature	Tstg		-30 to +125	°C

Operating Characteristics at Tc=25°C, R_L =4 Ω , R_g =600 Ω , VG=30dB, non-inductive load R_L , using constant-

voltage power supply and specification test circuit, unless otherwise specified

				-					-					
		Conditions *2				Conditions *2						Ratings	i	
Parameter	Symbol	V _{CC} (V)	f (Hz)	P _O (W)	THD (%)		min	typ	max	unit				
Output power *2	P _O (1)	±18	20 to 20k		0.4		10	15						
	P _O (2)	±18	1k		0.4			20		W				
	P _O (3)	±18.5	1k		10			30						
Total harmonic distortion *2	THD (1)	±18	20 to 20k	5.0		VG=30dB			0.4	%				
	THD (2)	±18	1k	5.0		VG=300B		0.08		%				
Output power transistor saturation voltage	Vsat	±18	1k	30	10			3.8		V				
Frequency characteristics *2	fL, fH	±18		1.0		+0 -3dB	+0 -3dB 20 to 50k		k	Hz				
Input impedance	ri	±18	1k	1.0				55		kΩ				
Output noise voltage *10	V _{NO}	±21.5				Rg=2.2kΩ			1.0	mVrms				
Quiescent current	ICCO	±21.5				No loading	12	25	50	mA				
Output neutral voltage	V _N	±21.5					-70	0	+70	mV				
Pin 13 voltage when standby ON *5	VST ON	±18				Standby		0	0.6	V				
Pin 13 voltage when standby OFF *5	VST OFF	±18				Operating	2.5	3.6	5.5	V				
Pin 10 (latch operation detection pin) voltage *7	IM ON					In short-circuit protection mode		6.2		V				
Substrate thermal protection *8	TD	±18	1k					125		°C				
Overcurrent protection *8,*10	IO (peak)	±18	1k					4.0		А				

[Remarks]

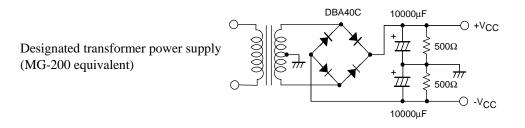
- *1: Maximum ratings are limits beyond which damage to the device may occur. Exceeding the maximum ratings, even momentarily, may cause damage to the hybrid IC. In SANYO Semiconductor's test processes, operation at the maximum supply voltage is checked. (Test conditions) V_{CC} max (2)=±25V, RL=4Ω, f=1kHz, Po=15W, 1ch Drive, ton=25ms, Tc=25°C
- *2: For 1-channel operation
- *3: -Pre V_{CC} (pin 1) must be connected to the lowest stable potential to prevent the current flowing into the pin 1 due to reverse bias, etc.
- *4: Thermal design must be implemented based on the conditions under which the customer's end products are expected to operate on the market.
- *5: Use the hybrid IC so that the voltage applied to the stand-by pin (pin 13) never exceeds the maximum rating. The power amplifier is turned on by applying +2.5V to +5.5V to the stand-by pin (pin 13).
- *6: An output limiting circuit for substrate overheating is incorporated to protect the hybrid IC from the heat generation exceeding the maximum rating. Thermal design must be implemented from the maximum loss Pd max and "Pd-Tc" derating curve based on the conditions under which the customer's end products are expected to operate on the market. When deviating from the "Pd-Tc" derating curve, the desired output is not obtained, but the prescribed output is generated again by reducing the substrate temperature to within the recommended operating region.
- *7: The load short-circuit protection is designed based on the specification test condition. The load short-circuit protection circuit is activated when it has detected an overcurrent in the output transistors. So if any deviation from the "Pd-Tc" derating curve occurs, the protection circuit is activated and the circuit shuts down in order to protect the output transistors. When the load short-circuit protection circuit has been activated and the circuit shuts down, approximately +6.2V of voltage will be placed at the MONITOR pin (pin 10) (normally 0V). The protection circuit operation is released by establishing the stand-by mode (pin 13: 0V).
- *8: The substrate temperature protection rating is the design guarantee value using the specification test circuit of SANYO Semiconductor.

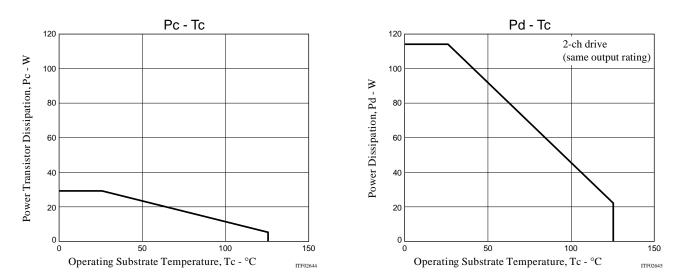
The output limiting circuit for substrate overheating (*6) and the load short-circuit protection circuit (*7) are the only protection functions incorporated.

The thermal design and overcurrent protection level must be verified based on the conditions under which the customer's end products are expected to operate on the market.

- *9: A thermoplastic adhesive resin is used to secure the case and aluminum substrate. For this reason, the hybrid IC must be fixed to the heat sink before soldering and mounted. The heat sink must be installed or removed at room temperature.
- *10: Use the designated transformer power supply circuit shown in the figure below for the measurement of allowable load shorted time and output noise voltage level.

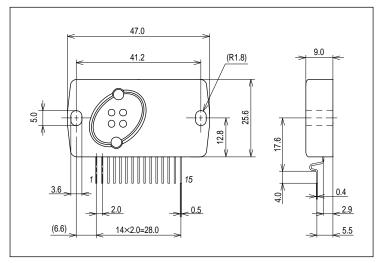
*11: Weight of independent hybrid IC: 12.2g Outer box dimensions: $452(D) \times 325(W) \times 192(H)$ mm



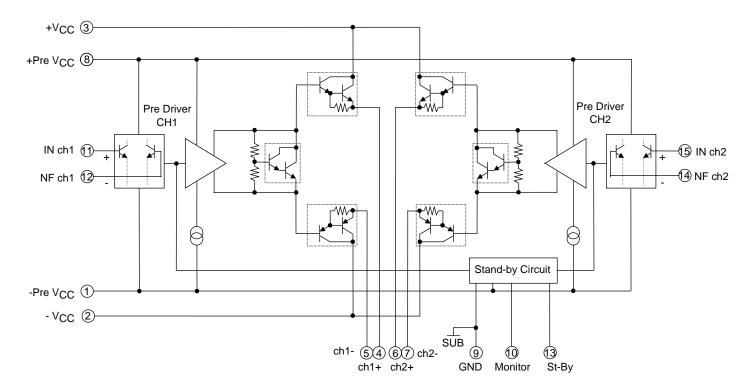


Package Dimensions

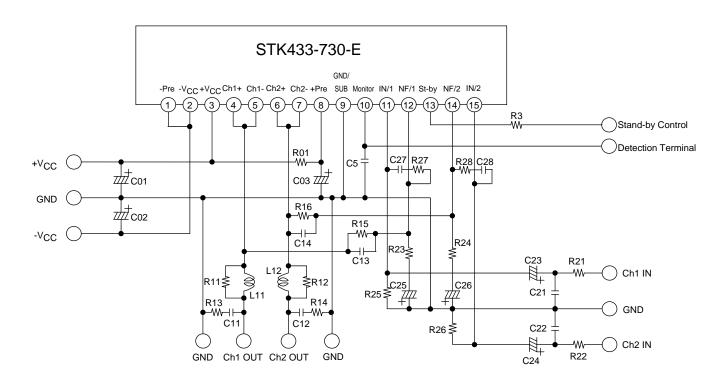
unit:mm (typ)



Internal Equivalent Circuit



Application Circuit Example

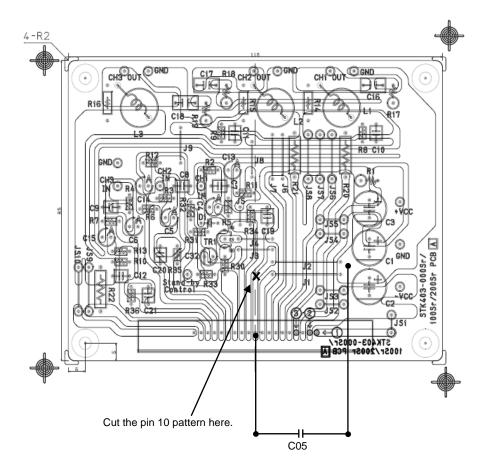


STK433-730-E

Symbol	Recommen	Description	Larger than	Smaller than				
-	ded Value		Recommended Value	Recommended Value				
R01	47Ω	Ripple filtering resistors (Fusible resistors are desirable)	Decreased pass-	Increased pass-				
		(Used with C03 to form a ripple filter.)	through current at high	through current at high				
			frequencies.	frequencies.				
R03	-	Use a limiting resistor according to the stand-by control voltage in or rating.	der to control the stand-by p	in voltage VST within the				
R11, 12	4.7Ω	Noise-absorbing resistors	-	-				
R13, 14	4.7Ω/1W	Oscillation prevention	-	-				
R15, 16	56kΩ	Used with R23 and R24 to determine the voltage gain VG.	VN offset					
			(Ensure R15=R25, R16=	R26 when changing.)				
R21, 22	1kΩ	Input filtering resistor	-	-				
R23, 24	1.8kΩ	Used with R15 and R16 to determine the voltage gain VG. (VG	Likely to oscillate	None				
		should desirably be determined by the R23 and R24 value.)	(VG<30dB)	(VG≤42dB)				
R25, 26	56kΩ	Input bias resistors (Virtually determine the input impedance.)	-	-				
R27, 28	3kΩ	Oscillation prevention	Likely to oscillate					
C01, 02	100µF	Oscillation prevention						
		Insert the capacitors as close to the IC as possible to decrease						
		the power impedance for reliable IC operation (use of	-	-				
		electrolytic capacitors are desirable).						
C03	200µF	Decoupling capacitors.	Increase in ripple compor	nents that pass into the				
		Eliminate ripple components that pass into the input side from	input side from the power	line.				
		the power line. (Used with R01 to form a filter.)						
C05	0.01µF	A detection voltage appears during the protection operation. Adjust used).	the time constant (when the	detection pin is to be				
C11, 12	0.1µF	Oscillation prevention (Mylar capacitors are recommended.)	Likely to oscillate					
C13, 14	12pF	Oscillation prevention	Likely to oscillate					
C21, 22	470pF	Input filter capacitor						
		(Used with R21 and R22 to form a filter that suppresses high-	-	-				
		frequency noises.)						
C23, 24	2.2µF	Input coupling capacitor (block DC current)	-	-				
C25, 26	10µF	NF capacitor	Increase in low-	Decrease in low-				
		(Changes the low cutoff frequency; $f_L=1/(2\pi \bullet C25 \bullet R23)$	frequency voltage gain,	frequency voltage gain				
			with higher pop noise					
			at power-on.					
C27, 28	2200pF	Oscillation prevention	Likely to oscillate					
L11, 12	1μH	Oscillation prevention	None	Likely to oscillate				

Recommended Values for Application Parts (for the test circuit)

Sample PCB Trace Pattern



* Additional components are indicated by their circuit location numbers.

STK433-730-E TEST Board PARTS LIST

STK403-000sr/100sr/200sr PCB

PCB Location No. CIRCUIT Location No.			PARTS	RATING	STK433-730-E		
R01 R01			ERG1SJ101	47Ω,1W			
R02,R03 R21, R22		RN16S102FK	1kΩ, 1/6W				
R05, R06, R08, F	809	R15, R16, R25, R26	RN16S563FK	56kΩ, 1/6W			
R11, R12		R23, R24	RN16S182FK	1.8kΩ, 1/6W			
R14, R15		R11, R12	RN14S4R7FK	4.7Ω, 1/4W			
R17, R18		R13, R14	ERX1SJ4R7	4.7Ω, 1W			
R20, R21		-	-	-	short		
R34, R35		R27, R28	RN16S561FK	3kΩ, 1/6W			
C01, C02		C01, C02	50MV100HC	100μF, 50V			
C03		C03	50MV200HC	200µF, 50V			
- C05			ECQ-V1H103JZ	0.01µF, 50V			
C05, C06 C23, C24		50MV2R2HC	2.2μF, 50V	(*)			
C07, C08 C21, C22		C21, C22	DD104-63B471K50	470pF, 50V			
C10, C11 C13, C14		DD104-63CJ120C50	12pF, 50V				
C13, C14 C25, C26		C25, C26	10MV10HC	10μF, 10V	(*)		
C16, C17		C11, C12	ECQ-V1H104JZ	0.1µF, 50V			
C19, C20 C27, C2		C27, C28	DD104-63B222K50	2200pF, 50V			
L01, L02		L11, L12	-				
Stand-By	Tr1		2SC2274(Reference)	VCE≥50V, IC≥10mA			
Control Circuit	R3		RN16S133FK	1kΩ, 1/6W			
	R31		RN16S333FK	33kΩ, 1/6W			
R33		RN16S202FK	2kΩ, 1/6W				
	C32		10MV33HC	33μF, 10V			
J1, J2, J3, J4, J5, J6, J8, J9		-	-	-	Jumper		
JS6		-	-	-	Jumper		
JS1		-	-	-	Jumper		

• (*) Capacitor mark "A" side is "-" (negative).

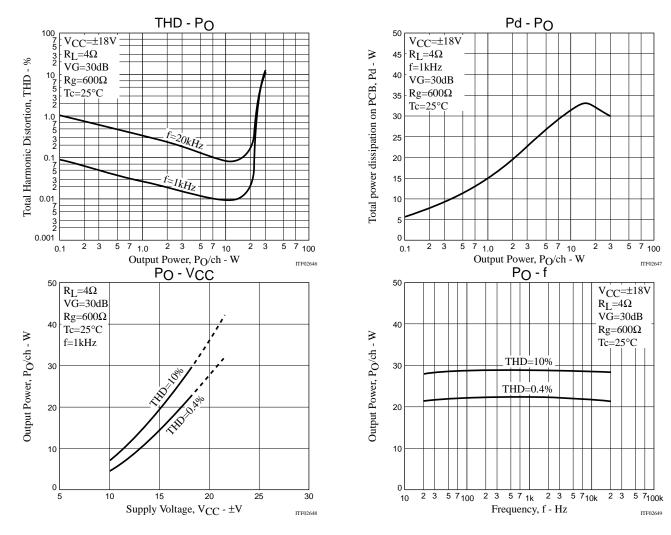
• C05 does not have a location number on the PCB so the component must be mounted on the reverse side of the board.

Pin Assignments

[STK433-730-E/-760-E Pin Layout]

	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19
(Size) 47.0mm×25.6mm×9.0mm						20	ch clas	sAB/2	2.00m	Im									
STK433-730-E 30W×2ch/JEITA	-	-	+	0	0	0	0	+		М	I	Ν	S	Ν	I				
STK433-760-E 50W×2ch/JEITA	Р	V	V	U	U	U	U	Р	s	0	Ν	F	Т	F	Ν				
	R	С	С	т	Т	Т	Т	R	U	Ν	/	/	А	/	/				
	Е	С	С	/	/	/	/	Е	В	1	С	С	Ν	С	С				
				С	С	С	С		/	Т	н	Н	D	н	н				
				н	н	н	н		G	0	1	1	Ι	2	2				
				1	1	2	2		Ν	R			В						
				+	-	+	-		D				Υ						

Evaluation Board Characteristics



[Thermal Design Example for STK433-730-E ($R_L = 4\Omega$)] The thermal resistance, θ c-a, of the heat sink for total power dissipation, Pd, within the hybrid IC is determined as follows. Condition 1: The hybrid IC substrate temperature, Tc, must not exceed 125°C. $Pd \times \theta c-a + Ta < 125^{\circ}C$ (1) Ta: Guaranteed ambient temperature for the end product Condition 2: The junction temperature, Tj, of each power transistor must not exceed 150°C. $Pd \times \theta c \cdot a + Pd/N \times \theta j \cdot c + Ta < 150^{\circ}C$ (2) N: Number of power transistors θj-c: Thermal resistance per power transistor However, the power dissipation, Pd, for the power transistors shall be allocated equally among the number of power transistors. The following inequalities result from solving equations (1) and (2) for θ c-a. $\theta c-a < (125 - Ta)/Pd$ (1) $\theta c-a < (150 - Ta)/Pd - \theta j-c/N$ (2) Values that satisfy these two inequalities at the same time represent the required heat sink thermal resistance. When the following specifications have been stipulated, the required heat sink thermal resistance can be determined from formulas (1)' and (2)'. VCC Supply voltage

• Supply voluge	
 Load resistance 	RL
• Guaranteed ambient temperature	Та

[Example]

When the IC supply voltage, V_{CC}, is $\pm 18V$ and R_L is 4 Ω , the total power dissipation, Pd, within the hybrid IC, will be a maximum of 33W at 1kHz for a continuous sine wave signal according to the Pd-P_O characteristics. For the music signals normally handled by audio amplifiers, a value of 1/8P_O max is generally used for Pd as an estimate of the power dissipation based on the type of continuous signal. (Note that the factor used may differ depending on the safety standard used.)

This is:

Pd = 24.09W (when 1/8PO max. = 3.75W).

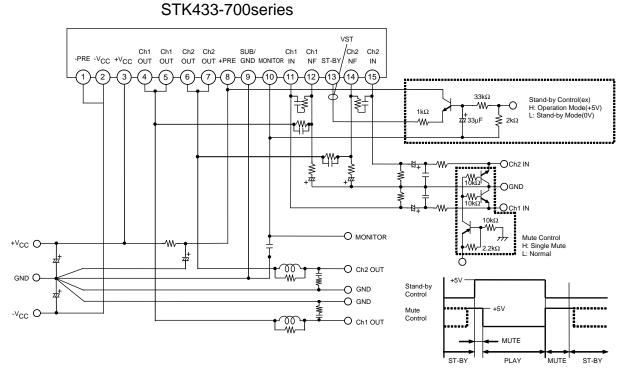
The number of power transistors in audio amplifier block of these hybrid ICs, N, is 4, and the thermal resistance per transistor, θ j-c, is 8.0°C/W. Therefore, the required heat sink thermal resistance for a guranteed ambient temperature, Ta, of 50°C will be as follows.

From formula (1)'	θ c-a < (125 - 50)/24.09
	< 3.11
From formula (2)'	θc -a < (150 - 50)/24.09 - 4.2/4
	< 3.10

Therefore, the value of 3.10°C/W, which satisfies both of these formulae, is the required thermal resistance of the heat sink.

Note that this thermal design example assumes the use of a constant-voltage power supply, and is therefore not a verified design for any particular user's end product.

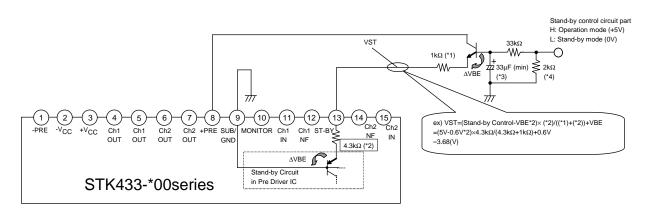
STK433-700series Stand-by Control & Mute Control Application



[The example of use STK433-*00series Stand-by control circuit]

Features

- By using the recommended stand-by control application, the pop noise level when the power is turned on/off can be significantly reduced.
- By adjusting the limiting resistance (*1) in accordance with the voltages of the microcontroller and other components used, it is possible to perform stand-by control, facilitating the finished product design effort. (ex) STK433-*00series test circuit. When impressed by Stand-by control control [+5V].



Operation Explanation

1) About VST (#13pin Stand-by Threshold)

<1> Operation Mode

When pin 13 reference voltage VST is equal to or greater than 2.5 V, the stand-by circuit is set OFF, and the amplifier is set to the operation mode.

<2> Stand-by Mode

When pin 13 reference voltage VST is equal to or less than 0.6V, the stand-by circuit is set ON, and the amplifier is set to the stand-by mode.

- (*3) The pop noise that occurs when the power is turned ON is reduced by providing a time constant using a capacitor during operation.
- (*4) The pop noise level is reduced by discharging the capacitor with a resistor in the stand-by mode.

- SANYO Semiconductor Co.,Ltd. assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all SANYO Semiconductor Co.,Ltd. products described or contained herein.
- SANYO Semiconductor Co.,Ltd. strives to supply high-quality high-reliability products, however, any and all semiconductor products fail or malfunction with some probability. It is possible that these probabilistic failures or malfunction could give rise to accidents or events that could endanger human lives, trouble that could give rise to smoke or fire, or accidents that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- In the event that any or all SANYO Semiconductor Co.,Ltd. products described or contained herein are controlled under any of applicable local export control laws and regulations, such products may require the export license from the authorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written consent of SANYO Semiconductor Co.,Ltd.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the SANYO Semiconductor Co.,Ltd. product that you intend to use.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production.
- Upon using the technical information or products described herein, neither warranty nor license shall be granted with regard to intellectual property rights or any other rights of SANYO Semiconductor Co.,Ltd. or any third party. SANYO Semiconductor Co.,Ltd. shall not be liable for any claim or suits with regard to a third party's intellectual property rights which has resulted from the use of the technical information and products mentioned above.

This catalog provides information as of May, 2009. Specifications and information herein are subject to change without notice.